contd B2

contacting a semiconducting organic material, and wherein the method is characterized by

depositing a first layer of a conducting material selected from the group consisting of calcium, manganese, aluminum, nickle, copper and silver or a semiconducting material selected from the group consisting of silicon, germanium, and gallium arsenide or a combination of a conducting and a semiconducting material in the form of a patterned or non-patterned layer on an insulating substrate, such that at least a portion of the substrate is covered by the first layer

modifying the work function of the conducting and/or semiconducting material of the first layer by depositing a second layer of a conducting polymer with a work function higher than that of the material in the first layer such that the layer of the conducting polymer mainly covers the first layer or is conformal with the latter, whereby the combination of the first layer and second layer constitutes the anode of the electrode arrangement and the work function of the anode becomes substantially equal to that of the conducting polymer,

depositing a third layer of semiconducting organic material on top of the anode, and optionally and in case only a portion of the substrate is covered by the anode, also above at least some of the portion of the substrate not covered by the anode, and